

# Alessandro Paccagnella

## List of Publications by Citations

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408  
papers

8,882  
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36  
h-index

82  
g-index

444  
ext. papers

9,973  
ext. citations

1.9  
avg, IF

5.2  
L-index

#	Paper	IF	Citations
4 <sup>08</sup>	THE LARGE AREA TELESCOPE ON THE FERMI GAMMA-RAY SPACE TELESCOPE MISSION. <i>Astrophysical Journal</i> , <b>2009</b> , 697, 1071-1102	4.7	2463
4 <sup>07</sup>	FERMI LARGE AREA TELESCOPE FIRST SOURCE CATALOG. <i>Astrophysical Journal, Supplement Series</i> , <b>2010</b> , 188, 405-436	8	754
4 <sup>06</sup>	Radiation induced leakage current and stress induced leakage current in ultra-thin gate oxides. <i>IEEE Transactions on Nuclear Science</i> , <b>1998</b> , 45, 2375-2382	1.7	135
4 <sup>05</sup>	Ionizing radiation induced leakage current on ultra-thin gate oxides. <i>IEEE Transactions on Nuclear Science</i> , <b>1997</b> , 44, 1818-1825	1.7	124
4 <sup>04</sup>	FERMI LARGE AREA TELESCOPE OBSERVATIONS OF THE VELA PULSAR. <i>Astrophysical Journal</i> , <b>2009</b> , 696, 1084-1093	4.7	111
4 <sup>03</sup>	Layout techniques to enhance the radiation tolerance of standard CMOS technologies demonstrated on a pixel detector readout chip. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2000</b> , 439, 349-360	1.2	108
4 <sup>02</sup>	The on-orbit calibration of the Fermi Large Area Telescope. <i>Astroparticle Physics</i> , <b>2009</b> , 32, 193-219	2.4	106
4 <sup>01</sup>	Radiation-Induced Short Channel (RISCE) and Narrow Channel (RINCE) Effects in 65 and 130 nm MOSFETs. <i>IEEE Transactions on Nuclear Science</i> , <b>2015</b> , 62, 2933-2940	1.7	104
4 <sup>00</sup>	Hydrated-layer formation during dissolution of complex silicate glasses and minerals. <i>Geochimica Et Cosmochimica Acta</i> , <b>1990</b> , 54, 1941-1955	5.5	99
399	Radiation Effects in Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2013</b> , 60, 1953-1969	1.7	87
398	Present and Future Non-Volatile Memories for Space. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> ,	1.7	84
397	Identification and classification of single-event upsets in the configuration memory of SRAM-based FPGAs. <i>IEEE Transactions on Nuclear Science</i> , <b>2003</b> , 50, 2088-2094	1.7	81
396	SVX', the new CDF silicon vertex detector. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>1995</b> , 360, 137-140	1.2	74
395	A New Hardware/Software Platform and a New 1/E Neutron Source for Soft Error Studies: Testing FPGAs at the ISIS Facility. <i>IEEE Transactions on Nuclear Science</i> , <b>2007</b> , 54, 1184-1189	1.7	70
394	. <i>IEEE Transactions on Electron Devices</i> , <b>1992</b> , 39, 1849-1857	2.9	69
393	Radiation effects on floating-gate memory cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2001</b> , 48, 2222-2228	1.7	68
392	Aspect ratio calculation in n-channel MOSFETs with a gate-enclosed layout. <i>Solid-State Electronics</i> , <b>2000</b> , 44, 981-989	1.7	62

391	Facility for fast neutron irradiation tests of electronics at the ISIS spallation neutron source. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 114101	3.4	56
390	Low field leakage current and soft breakdown in ultra-thin gate oxides after heavy ions, electron or X-ray irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2000</b> , 47, 566-573	1.7	54
389	Transient conductive path induced by a Single ion in 10 nm SiO/sub 2/ Layers. <i>IEEE Transactions on Nuclear Science</i> , <b>2004</b> , 51, 3304-3311	1.7	53
388	A model of radiation induced leakage current (RILC) in ultra-thin gate oxides. <i>IEEE Transactions on Nuclear Science</i> , <b>1999</b> , 46, 1553-1561	1.7	53
387	Properties of SiO <sub>2</sub> /Si/GaAs structures formed by solid phase epitaxy of amorphous Si on GaAs. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 2540-2542	3.4	52
386	Influence of LDD Spacers and H <sup>+</sup> Transport on the Total-Ionizing-Dose Response of 65-nm MOSFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , <b>2018</b> , 65, 164-174	1.7	51
385	Silver nanoparticles inkjet-printed flexible biosensor for rapid label-free antibiotic detection in milk. <i>Sensors and Actuators B: Chemical</i> , <b>2019</b> , 280, 280-289	8.5	49
384	A model for TID effects on floating Gate Memory cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2004</b> , 51, 3753-3758	1.7	46
383	. <i>IEEE Transactions on Nuclear Science</i> , <b>2000</b> , 47, 2648-2655	1.7	46
382	Structural dependence of crystalline silicate hydration during aqueous dissolution. <i>Earth and Planetary Science Letters</i> , <b>1989</b> , 93, 292-298	5.3	44
381	Radiation induced leakage current in floating gate memory cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2005</b> , 52, 2144-2152	1.7	43
380	Anomalous charge loss from floating-gate memory cells due to heavy ions irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2002</b> , 49, 3051-3058	1.7	43
379	Key Contributions to the Cross Section of NAND Flash Memories Irradiated With Heavy Ions. <i>IEEE Transactions on Nuclear Science</i> , <b>2008</b> , 55, 3302-3308	1.7	42
378	Evaluating the effects of SEUs affecting the configuration memory of an SRAM-based FPGA		41
377	Hydrogen bonding in amorphous silicon with use of the low-pressure chemical-vapor-deposition technique. <i>Physical Review B</i> , <b>1991</b> , 43, 6627-6632	3.3	39
376	Error Instability in Floating Gate Flash Memories Exposed to TID. <i>IEEE Transactions on Nuclear Science</i> , <b>2009</b> , 56, 3267-3273	1.7	38
375	Accelerated wear-out of ultra-thin gate oxides after irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2003</b> , 50, 729-734	1.7	37
374	Schottky diodes on hydrogen plasma treated n-GaAs surfaces. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 259-261	3.4	37

373	. <i>IEEE Electron Device Letters</i> , <b>1990</b> , 11, 487-489	4.4	37
372	Charge loss after <sup>60</sup> Co irradiation of flash arrays. <i>IEEE Transactions on Nuclear Science</i> , <b>2004</b> , 51, 2912-2916	1.7	36
371	Deep submicron CMOS technologies for the LHC experiments. <i>Nuclear Physics, Section B, Proceedings Supplements</i> , <b>1999</b> , 78, 625-634		36
370	Evidence of interface trap creation by hot-electrons in AlGaAs/GaAs high electron mobility transistors. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1411-1413	3.4	36
369	TID Sensitivity of NAND Flash Memory Building Blocks. <i>IEEE Transactions on Nuclear Science</i> , <b>2009</b> , 56, 1909-1913	1.7	35
368	Angular Dependence of Heavy Ion Effects in Floating Gate Memory Arrays. <i>IEEE Transactions on Nuclear Science</i> , <b>2007</b> , 54, 2371-2378	1.7	35
367	Data retention after heavy ion exposure of floating gate memories: analysis and simulation. <i>IEEE Transactions on Nuclear Science</i> , <b>2003</b> , 50, 2176-2183	1.7	35
366	Gate Bias Dependence of Defect-Mediated Hot-Carrier Degradation in GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 1316-1320	2.9	34
365	Effect of different total ionizing dose sources on charge loss from programmed floating gate cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2005</b> , 52, 2372-2377	1.7	34
364	. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2004</b> , 4, 359-370	1.6	34
363	Heavy-Ion Induced Threshold Voltage Tails in Floating Gate Arrays. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> ,	1.7	33
362	Catastrophic Failure in Highly Scaled Commercial NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> , 57, 266-271	1.7	33
361	A model of the stress induced leakage current in gate oxides. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 285-288	2.9	33
360	Radiation tolerance of single-sided silicon microstrips. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>1994</b> , 339, 511-523 <sup>1,2</sup>		33
359	Annealing of Heavy-Ion Induced Floating Gate Errors: LET and Feature Size Dependence. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> , 57, 1835-1841	1.7	32
358	Impact of Technology Scaling on the Heavy-Ion Upset Cross Section of Multi-Level Floating Gate Cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 969-974	1.7	32
357	Drain current decrease in MOSFETs after heavy ion irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2004</b> , 51, 3150-3157	1.7	30
356	Noise characteristics of radiation-induced soft breakdown current in ultrathin gate oxides. <i>IEEE Transactions on Nuclear Science</i> , <b>2001</b> , 48, 2093-2100	1.7	30

355	Ion beam testing of ALTERA APEX FPGAs		30
354	Effects of Heavy-Ion Irradiation on Vertical 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2018</b> , 65, 318-325	1.7	29
353	Simulation-based analysis of SEU effects in SRAM-based FPGAs. <i>IEEE Transactions on Nuclear Science</i> , <b>2004</b> , 51, 3354-3359	1.7	29
352	Study of breakdown effects in silicon multiguard structures. <i>IEEE Transactions on Nuclear Science</i> , <b>1999</b> , 46, 1215-1223	1.7	29
351	Total Ionizing Dose Effects in NOR and NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2007</b> , 54, 1066-1070	1.7	28
350	. <i>IEEE Transactions on Electron Devices</i> , <b>2002</b> , 49, 1367-1374	2.9	28
349	Enhancement of Transistor-to-Transistor Variability Due to Total Dose Effects in 65-nm MOSFETs. <i>IEEE Transactions on Nuclear Science</i> , <b>2015</b> , 62, 2398-2403	1.7	26
348	Increase in the Heavy-Ion Upset Cross Section of Floating Gate Cells Previously Exposed to TID. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> ,	1.7	26
347	Subpicosecond conduction through thin SiO <sub>2</sub> layers triggered by heavy ions. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 074101	2.5	26
346	Ionizing radiation effects on floating gates. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 485-487	3.4	26
345	Impact of Aging Phenomena on Soft Error Susceptibility <b>2011</b> ,		23
344	Space and time-resolved gene expression experiments on cultured mammalian cells by a single-cell electroporation microarray. <i>New Biotechnology</i> , <b>2008</b> , 25, 55-67	6.4	23
343	Single and Multiple Cell Upsets in 25-nm NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2013</b> , 60, 2675-2681	1.7	22
342	. <i>IEEE Electron Device Letters</i> , <b>1992</b> , 13, 253-255	4.4	22
341	Angular Dependence of Heavy-Ion Induced Errors in Floating Gate Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 2621-2627	1.7	21
340	Channel Hot Carrier Stress on Irradiated 130-nm NMOSFETs. <i>IEEE Transactions on Nuclear Science</i> , <b>2008</b> , 55, 1960-1967	1.7	21
339	Total dose dependence of radiation-induced leakage current in ultra-thin gate oxides. <i>Microelectronics Reliability</i> , <b>1999</b> , 39, 221-226	1.2	21
338	. <i>IEEE Transactions on Electron Devices</i> , <b>1991</b> , 38, 2571-2573	2.9	21

337	Metal-GaAs interaction and contact degradation in microwave MESFETs. <i>Quality and Reliability Engineering International</i> , <b>1990</b> , 6, 29-46	2.6	21
336	Pd/Ge ohmic contacts for GaAs metal-semiconductor field effect transistors: Technology and performance. <i>Thin Solid Films</i> , <b>1990</b> , 187, 9-18	2.2	21
335	Impact of Bias Temperature Instability on Soft Error Susceptibility. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , <b>2015</b> , 23, 743-751	2.6	20
334	Sample-to-Sample Variability and Bit Errors Induced by Total Dose in Advanced NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2014</b> , 61, 2889-2895	1.7	20
333	Potential High Resolution Dosimeters For MRT <b>2010</b> ,		20
332	Degradation of Sub 40-nm NAND Flash Memories Under Total Dose Irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2012</b> , 59, 2952-2958	1.7	20
331	Radiation effects on breakdown characteristics of multiguarded devices. <i>IEEE Transactions on Nuclear Science</i> , <b>1997</b> , 44, 721-727	1.7	20
330	Impact of Heavy-Ion Strikes on Minimum-Size MOSFETs With Ultra-Thin Gate Oxide. <i>IEEE Transactions on Nuclear Science</i> , <b>2006</b> , 53, 3675-3680	1.7	20
329	Potentials and pitfalls of FPGA application in inverter drives - a case study		20
328	New results on silicon microstrip detectors of CMS tracker. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2000</b> , 447, 142-150	1.2	20
327	. <i>IEEE Transactions on Electron Devices</i> , <b>1991</b> , 38, 2682-2684	2.9	20
326	Silicon diffusion in aluminium. <i>Thin Solid Films</i> , <b>1985</b> , 128, 217-223	2.2	20
325	Total-Ionizing-Dose Effects and Low-Frequency Noise in 16-nm InGaAs FinFETs With HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Dielectrics. <i>IEEE Transactions on Nuclear Science</i> , <b>2020</b> , 67, 210-220	1.7	20
324	Total Ionizing Dose Effects in 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2019</b> , 66, 48-53	1.7	20
323	Effects of high energy x ray and proton irradiation on lead zirconate titanate thin films' dielectric and piezoelectric response. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 192906	3.4	19
322	Stress induced leakage current in ultra-thin gate oxides after constant current stress. <i>Microelectronic Engineering</i> , <b>1997</b> , 36, 145-148	2.5	19
321	Impact of 24-GeV Proton Irradiation on 0.13- $\mu$ m CMOS Devices. <i>IEEE Transactions on Nuclear Science</i> , <b>2006</b> , 53, 1917-1922	1.7	19
320	Single Event Effects in NAND Flash Memory Arrays. <i>IEEE Transactions on Nuclear Science</i> , <b>2006</b> , 53, 1813-1818	1.8	19

319	. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2004</b> , 4, 63-72	1.6	19
318	Gate current in ultrathin MOS capacitors: a new model of tunnel current. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 271-278	2.9	19
317	Silicon avalanche detectors with negative feedback as detectors for high energy physics. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>1995</b> , 367, 212-214	1.2	19
316	Impact ionization, recombination, and visible light emission in AlGaAs/GaAs high electron mobility transistors). <i>Journal of Applied Physics</i> , <b>1991</b> , 70, 529-531	2.5	19
315	Dose-Rate Sensitivity of 65-nm MOSFETs Exposed to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , <b>2018</b> , 65, 1482-1487	1.7	19
314	Using AFM Related Techniques for the Nanoscale Electrical Characterization of Irradiated Ultrathin Gate Oxides. <i>IEEE Transactions on Nuclear Science</i> , <b>2007</b> , 54, 1891-1897	1.7	18
313	High-resistance buried layers by MeV Fe implantation in n-type InP. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 668-670	3.4	18
312	Dissolution mechanisms of silicate minerals yielded by intercomparison with glasses and radiation damage studies. <i>Chemical Geology</i> , <b>1989</b> , 78, 219-227	4.2	18
311	Influence of Halo Implantations on the Total Ionizing Dose Response of 28-nm pMOSFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , <b>2019</b> , 66, 82-90	1.7	18
310	Charge Buildup and Spatial Distribution of Interface Traps in 65-nm pMOSFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , <b>2019</b> , 66, 1574-1583	1.7	17
309	Possible effects on avionics induced by terrestrial gamma-ray flashes. <i>Natural Hazards and Earth System Sciences</i> , <b>2013</b> , 13, 1127-1133	3.9	17
308	MRS detectors with high gain for registration of weak visible and UV light fluxes. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>1997</b> , 387, 225-230	1.2	17
307	Soft breakdown current noise in ultra-thin gate oxides. <i>Solid-State Electronics</i> , <b>2002</b> , 46, 1019-1025	1.7	17
306	Sorption of Actinide Analogues on Granite Minerals Studied by MeV Ion Beam Techniques. <i>Radiochimica Acta</i> , <b>1988</b> , 44-45, 299-304	1.9	17
305	Temperature dependence of neutron-induced soft errors in SRAMs. <i>Microelectronics Reliability</i> , <b>2012</b> , 52, 289-293	1.2	16
304	Drain Current Collapse in 65 nm pMOS Transistors After Exposure to Grad Dose. <i>IEEE Transactions on Nuclear Science</i> , <b>2015</b> , 62, 2899-2905	1.7	16
303	Effects of Total Ionizing Dose on the Retention of 41-nm NAND Flash Cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 2824-2829	1.7	16
302	Microdose and Breakdown Effects Induced by Heavy Ions on Sub 32-nm Triple-Gate SOI FETs. <i>IEEE Transactions on Nuclear Science</i> , <b>2008</b> , 55, 3182-3188	1.7	16

301	Collapse of MOSFET drain current after soft breakdown and its dependence on the transistor aspect ratio W/L		16
300	Statistical model for radiation-induced wear-out of ultra-thin gate oxides after exposure to heavy ion irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2003</b> , 50, 2167-2175	1.7	16
299	. <i>IEEE Electron Device Letters</i> , <b>1991</b> , 12, 80-81	4.4	16
298	Ionizing-Radiation Response and Low-Frequency Noise of 28-nm MOSFETs at Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , <b>2020</b> , 67, 1302-1311	1.7	15
297	. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2012</b> , 12, 437-444	1.6	15
296	Channel-Hot-Carrier Degradation and Bias Temperature Instabilities in CMOS Inverters. <i>IEEE Transactions on Electron Devices</i> , <b>2009</b> , 56, 2155-2159	2.9	15
295	Degradation Induced by X-Ray Irradiation and Channel Hot Carrier Stresses in 130-nm NMOSFETs With Enclosed Layout. <i>IEEE Transactions on Nuclear Science</i> , <b>2008</b> , 55, 3216-3223	1.7	15
294	Post-radiation-induced soft breakdown conduction properties as a function of temperature. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 1336-1338	3.4	15
293	A novel approach to quantum point contact for post soft breakdown conduction		15
292	Degradation mechanism of Ti/Au and Ti/Pd/Au gate metallizations in GaAs MESFET's. <i>IEEE Transactions on Electron Devices</i> , <b>1987</b> , 34, 957-960	2.9	15
291	CHIPIX65: Developments on a new generation pixel readout ASIC in CMOS 65 nm for HEP experiments <b>2015</b> ,		14
290	Impact of NBTI Aging on the Single-Event Upset of SRAM Cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> ,	1.7	14
289	Methodologies to Study Frequency-Dependent Single Event Effects Sensitivity in Flash-Based FPGAs. <i>IEEE Transactions on Nuclear Science</i> , <b>2009</b> , 56, 3534-3541	1.7	14
288	Systematic characterization of soft- and hard-breakdown spots using techniques with nanometer resolution. <i>Microelectronic Engineering</i> , <b>2007</b> , 84, 1956-1959	2.5	14
287	Electrical stresses on ultra-thin gate oxide SOI MOSFETs after irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2005</b> , 52, 2252-2258	1.7	14
286	Secondary Effects of Single Ions on Floating Gate Memory Cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2006</b> , 53, 3291-3297	1.7	14
285	Thin oxide degradation after high-energy ion irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2001</b> , 48, 1735-1743	1.7	14
284	GaAs MESFETs with nonalloyed ohmic contacts: technology and performance. <i>Electronics Letters</i> , <b>1988</b> , 24, 708-709	1.1	14



283	Mechanical properties of ion implanted glasses. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1984</b> , 1, 253-257	1.2	14
282	Developments on DC/DC converters for the LHC experiment upgrades. <i>Journal of Instrumentation</i> , <b>2014</b> , 9, C02017-C02017	1	13
281	Space Environment Effects on Flexible, Low-Voltage Organic Thin-Film Transistors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 35150-35158	9.5	13
280	Total Ionizing Dose effects on a 28 nm Hi-K metal-gate CMOS technology up to 1 Grad. <i>Journal of Instrumentation</i> , <b>2017</b> , 12, C02003-C02003	1	13
279	Single Event Effects in 90-nm Phase Change Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 2755-2760	1.7	13
278	Effect of Ion Energy on Charge Loss From Floating Gate Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2008</b> , 55, 2042-2047	1.7	13
277	Effectiveness of TMR-Based Techniques to Mitigate Alpha-Induced SEU Accumulation in Commercial SRAM-Based FPGAs. <i>IEEE Transactions on Nuclear Science</i> , <b>2008</b> , 55, 1968-1973	1.7	13
276	. <i>IEEE Transactions on Electron Devices</i> , <b>1990</b> , 37, 1163-1165	2.9	13
275	Correlation between impact ionisation, recombination and visible light emission in GaAs MESFETs. <i>Electronics Letters</i> , <b>1991</b> , 27, 770	1.1	13
274	Single Event Upsets Induced by Direct Ionization from Low-Energy Protons in Floating Gate Cells. <i>IEEE Transactions on Nuclear Science</i> , <b>2017</b> , 64, 464-470	1.7	12
273	Space and terrestrial radiation effects in flash memories. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 033003	1.8	12
272	Gate Bias and Length Dependences of Total Ionizing Dose Effects in InGaAs FinFETs on Bulk Si. <i>IEEE Transactions on Nuclear Science</i> , <b>2019</b> , 66, 1599-1605	1.7	12
271	Neutron and Alpha Single Event Upsets in Advanced NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , <b>2014</b> , 61, 1799-1805	1.7	12
270	Power converters for future LHC experiments. <i>Journal of Instrumentation</i> , <b>2012</b> , 7, C03012-C03012	1	12
269	Reliability extrapolation model for stress-induced-leakage current in thin silicon oxides. <i>Electronics Letters</i> , <b>1997</b> , 33, 1342	1.1	12
268	On the Evaluation of Radiation-Induced Transient Faults in Flash-Based FPGAs <b>2008</b> ,		12
267	Effects of Heavy-Ion Strikes on Fully Depleted SOI MOSFETs With Ultra-Thin Gate Oxide and Different Strain-Inducing Techniques. <i>IEEE Transactions on Nuclear Science</i> , <b>2007</b> , 54, 2257-2263	1.7	12
266	Variability in FG Memories Performance After Irradiation. <i>IEEE Transactions on Nuclear Science</i> , <b>2006</b> , 53, 3349-3355	1.7	12

265	Comparison of the electrical and thermal stability of stress- or radiation-induced leakage current in thin oxides. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1158-1160	3.4	12
264	Electron irradiation effects on thin MOS capacitors. <i>Journal of Non-Crystalline Solids</i> , <b>1999</b> , 245, 238-244	3.9	12
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